



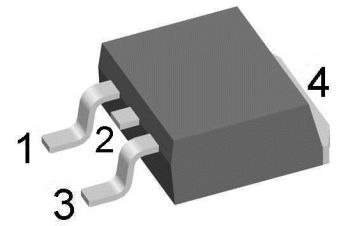
FRED

V_{RRM}	=	600 V
I_{FAV}	=	30 A
t_{rr}	=	35 ns

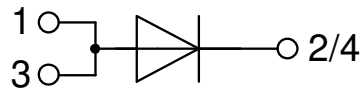
Fast Recovery Epitaxial Diode Single Diode

Part number

DSEI36-06AS



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

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Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			600	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			600	V	
I_R	reverse current, drain current	$V_R = 600 V$	$T_{VJ} = 25^{\circ}C$		100	μA	
		$V_R = 480 V$	$T_{VJ} = 125^{\circ}C$		7	mA	
V_F	forward voltage drop	$I_F = 30 A$	$T_{VJ} = 25^{\circ}C$		1.54	V	
		$I_F = 60 A$			1.74	V	
		$I_F = 30 A$	$T_{VJ} = 150^{\circ}C$		1.38	V	
		$I_F = 60 A$			1.67	V	
I_{FAV}	average forward current	$T_C = 110^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}C$		30	A	
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		1.10	V	
r_F	slope resistance				9.1	m Ω	
R_{thJC}	thermal resistance junction to case				0.8	K/W	
R_{thCH}	thermal resistance case to heatsink			0.25		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		155	W	
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		300	A	
C_J	junction capacitance	$V_R = 600 V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		22	pF	
I_{RM}	max. reverse recovery current	} $I_F = 37 A; V_R = 350 V$ $-di_F/dt = 200 A/\mu s$	$T_{VJ} = 25^{\circ}C$		5.5	A	
			$T_{VJ} = 100^{\circ}C$		9	A	
t_{rr}	reverse recovery time		$T_{VJ} = 25^{\circ}C$		80	ns	
			$T_{VJ} = 100^{\circ}C$		150	ns	



Package TO-263 (D2Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			35	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				1.5		g
F_C	mounting force with clip		20		60	N

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI36-06AS-TRL	DSEI36-06AS-TRL	Tape & Reel	800	500059
Alternative	DSEI36-06AS-TUB	DSEI36-06AS	Tube	50	469114

Equivalent Circuits for Simulation

** on die level*

$T_{VJ} = 150^{\circ}C$



Fast Diode

$V_{0\ max}$	threshold voltage	1.1	V
$R_{0\ max}$	slope resistance *	6	mΩ

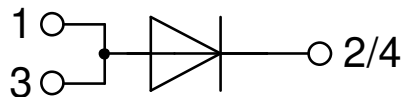


Outlines TO-263 (D2Pak)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.5		0.098	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with and/or within JEDEC standard.



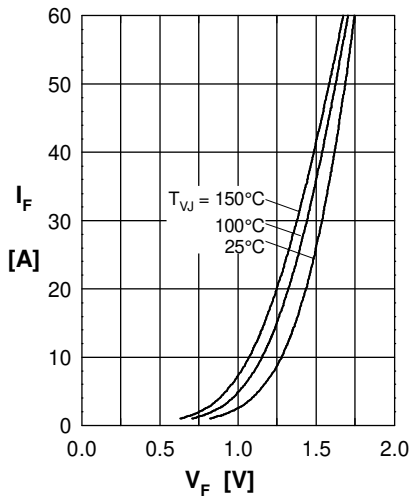
Fast Diode


Fig. 1 Forward current versus max. forward voltage drop

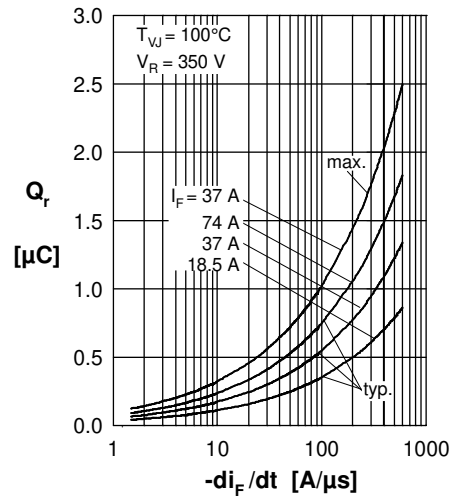
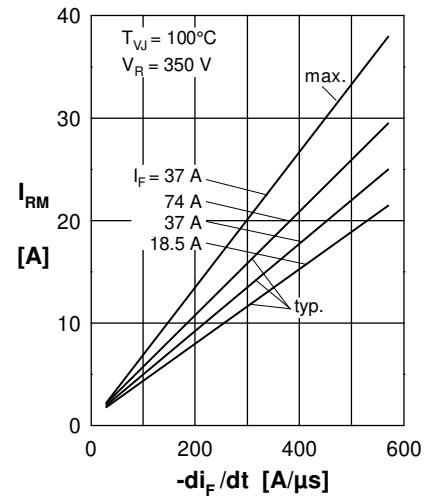
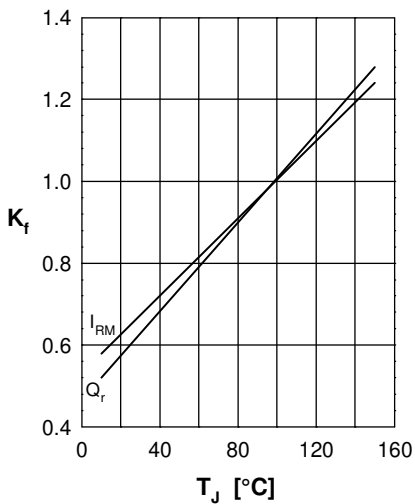

 Fig. 2 Recovery charge versus $-di_F/dt$

 Fig. 3 Peak reverse current versus $-di_F/dt$


Fig. 4 Dynamic parameters vs. junction temperature

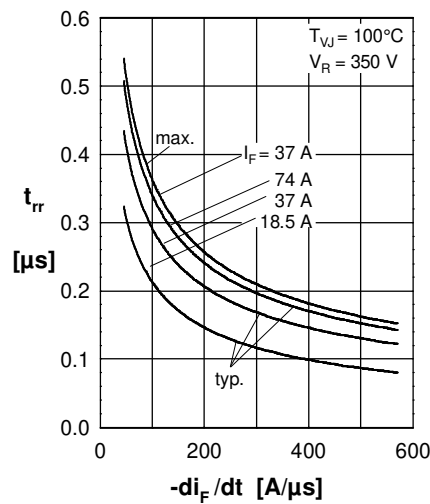
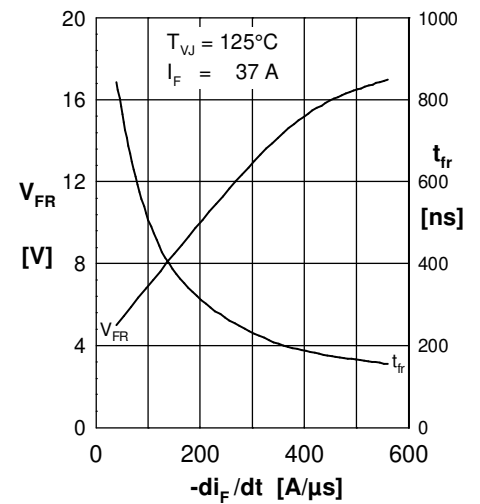
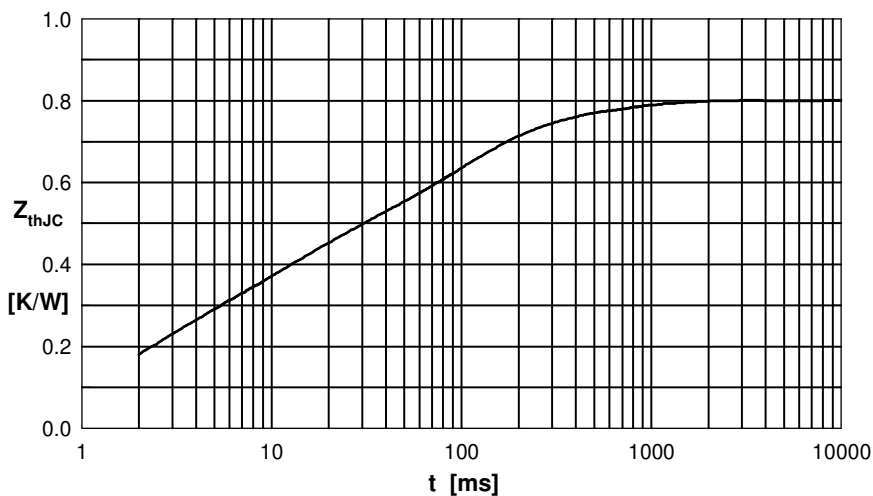

 Fig. 5 Recovery time versus $-di_F/dt$

 Fig. 6 Peak forward voltage versus $-di_F/dt$


Fig. 7 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.200	0.0018
2	0.220	0.0100
3	0.080	0.5000
4	0.300	0.0900